

# Specification Sheet

P Type Silicon Wafer

(4" Boron Doping)

Stock No: NS6130-10-1002, CAS: 7440-21-3

<b>Product</b>	:	<b>Silicon Wafer 4"</b>
Stock No	:	NS6130-10-1002
CAS	:	7440-21-3
Diameter	:	4"
Thickness	:	450 $\mu$ m
Dopant	:	Boron
Crystal Orientation	:	< 100>
Type	:	P
Growth Method	:	CZ
Resistivity	:	1.0-5.0 $\Omega$ .cm
TTV	:	< 10 $\mu$ m
STIR	:	< 2 $\mu$ m
GLOBAL TIR	:	< 5 $\mu$ m
LPD	:	< 30 counts @ particles size>0.3 $\mu$ m
Laser Mark	:	None
Edge Profile	:	Rounded
Front Surface	:	Polished
Back Surface	:	Etched
Bow	:	30 $\mu$ m
<b>Main Inspect Verifier</b>	:	<b>Manager QC</b>

**Note:** Product Specification are subject to amendment and may change over time

## Characterization of P Type Silicon Wafer



P Type Silicon Wafer



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